

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A semiconductor light-receiving device comprising:
a semiconductor substrate having a first surface on a light-receiving side and a second surface on the opposite side to said first surface, said semiconductor substrate comprising a first conductivity type;
a semiconductor layer formed on said first surface of said semiconductor substrate;
a plurality of first semiconductor regions formed in said semiconductor layer so as to reach said semiconductor substrate from a surface of said semiconductor layer, said plurality of first semiconductor regions being formed apart from each other, and comprising the first conductivity type;
a second semiconductor region selectively formed in a surface region of said semiconductor layer, said second semiconductor region having a lattice form or a network form to surround surrounding each of said plurality of first semiconductor regions with a surface portion of said semiconductor layer therebetween and comprising a second conductivity type;
a first electrode formed on said second semiconductor region and having a lattice form or a network form; and
a second electrode formed on said second surface of said semiconductor substrate;
said surface portion of said semiconductor layer between each of said plurality of first semiconductor regions and said second semiconductor region having a higher resistance than resistances of said plurality of first semiconductor regions and said second semiconductor region.

Claims 2 and 3 (Canceled).

Claim 4 (Previously Presented): The semiconductor light-receiving device according to Claim 1, wherein said first electrode is formed on part of said second semiconductor region.

Claim 5 (Previously Presented): The semiconductor light-receiving device according to Claim 1, wherein each of said plurality of first semiconductor regions has an island form or a stripe form.

Claim 6 (Previously Presented): The semiconductor light-receiving device according to Claim 1, wherein the surface portion of said semiconductor layer between said second semiconductor region and each of said plurality of first semiconductor layers is completely depleted in a state in which a reverse bias is applied between said first electrode and said second electrode.

Claim 7 (Currently Amended): A semiconductor light-receiving device comprising:
a semiconductor substrate having a first surface on a light-receiving side and a second surface on the opposite side to said first surface, said semiconductor substrate comprising a first conductivity type;
a semiconductor layer formed on said first surface of said semiconductor substrate;
a plurality of first semiconductor regions formed in said semiconductor layer so as to reach said semiconductor substrate from a surface of said semiconductor layer, said plurality

of first semiconductor regions being formed apart from each other, and comprising the first conductive conductivity type;

a second semiconductor region selectively formed in a surface region of said semiconductor layer and having a plurality of openings, each of said plurality of first semiconductor regions being provided within each of said plurality of openings of said second semiconductor region respectively with a surface portion of said semiconductor layer therebetween and comprising a second conductivity type;

a first electrode formed on said second semiconductor region and having a lattice form or a network form; and

a second electrode formed on said second surface of said semiconductor substrate; said surface portion of said semiconductor layer between each of said plurality of first semiconductor regions and said second semiconductor region having has a higher resistance than resistances of said plurality of first semiconductor regions and said second semiconductor region.

Claim 8 (Canceled).

Claim 9 (Previously Presented): The semiconductor light-receiving device according to Claim 7, wherein said first electrode is formed on part of said second semiconductor region.

Claim 10 (Previously Presented): The semiconductor light-receiving device according to Claim 7, wherein each of said plurality of first semiconductor regions has an island form or a stripe form.

Claim 11 (Previously Presented): The semiconductor light-receiving device according to Claim 7, wherein the surface portion of said semiconductor layer between said second semiconductor region and each of said plurality of first semiconductor regions is completely depleted in a state in which a reverse bias is applied between said first electrode and said second electrode.

Claim 12 (Currently Amended): A semiconductor light-receiving device comprising: a semiconductor substrate having a first surface on a light-receiving side and a second surface on the opposite side to said first surface, said first surface including a plurality of protruded surface portions separated from each other, and said semiconductor substrate comprising a first conductivity type;

a semiconductor layer selectively formed on said first surface of said semiconductor substrate, said semiconductor layer having a higher resistance than a resistance of said semiconductor substrate and having a plurality of openings, each of said plurality of protruded surface portions of said first surface being positioned within each of said plurality of openings of said semiconductor layer respectively;

a semiconductor region selectively formed in a surface region of said semiconductor layer and having a lattice form or a network form to surround surrounding each of said plurality of protruded surface portions of said first surface with a surface portion of said semiconductor layer therebetween, said semiconductor region comprising a second conductivity type;

a first electrode formed on said semiconductor region and having a lattice form or a network form; and

a second electrode formed on said second surface of said semiconductor substrate.

Claims 13 and 14 (Canceled).

Claim 15 (Previously Presented): The semiconductor light-receiving device according to Claim 12, wherein said first electrode is formed on part of said semiconductor region.

Claim 16 (Previously Presented): The semiconductor light-receiving device according to Claim 12, wherein each of said plurality of protruded surface portions of said semiconductor substrate has an island form or a stripe form.

Claim 17 (Previously Presented): The semiconductor light receiving device according to Claim 12, wherein said surface portion of said semiconductor layer between said semiconductor region and each of said plurality of protruded surface portions of said semiconductor substrate is completely depleted in a state in which a reverse bias is applied between said first electrode and said second electrode.

Claim 18 (Currently Amended): A semiconductor light-receiving device comprising:
a semiconductor substrate having a first surface on a light-receiving side and a second surface on the opposite side to said first surface, said first surface including a plurality of protruded surface portions separated from each other, and said semiconductor substrate comprising a first conductivity type;
a semiconductor layer selectively formed on said first surface of said semiconductor substrate, said semiconductor layer having a higher resistance than a resistance of said semiconductor substrate and having a plurality of openings, each of said plurality of

protruded surface portions of said first surface being positioned within each of said plurality of openings of said semiconductor layer respectively;

a semiconductor region selectively formed in a surface region of said semiconductor layer and having a plurality of openings, each of said plurality of protruded surface portions of said first surface being provided within each of said plurality of openings of said semiconductor region respectively with a surface portion of said ~~first~~ semiconductor layer therebetween, and said semiconductor region comprising a second conductivity type;

a first electrode formed on said semiconductor region and having a lattice form or a network form; and

a second electrode formed on said second surface of said semiconductor substrate.

Claim 19 (Canceled).

Claim 20 (Previously Presented): The semiconductor light-receiving device according to claim 18, wherein said first electrode is formed on part of said semiconductor region.

Claim 21 (Previously Presented): The semiconductor light-receiving device according to claim 18, wherein each of said plurality of protruded surface portions of said semiconductor substrate has an island form or a stripe form.

Claim 22 (Previously Presented): The semiconductor light-receiving device according to claim 18, wherein said surface portion of said semiconductor layer between said semiconductor region and each of said plurality of protruded surface portions of said

semiconductor substrate is completely depleted in a state in which a reverse bias is applied between said first electrode and said second electrode.